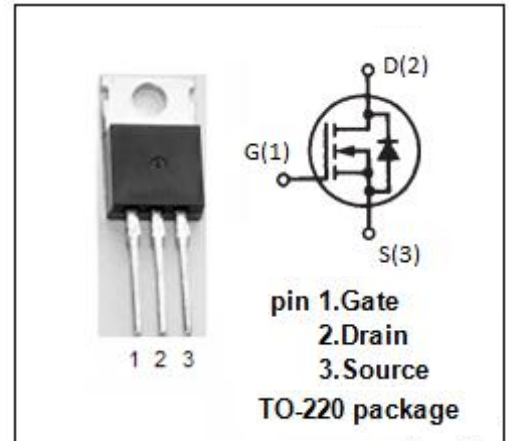


**isc N-Channel MOSFET Transistor**
**STP8NM60**
**FEATURES**

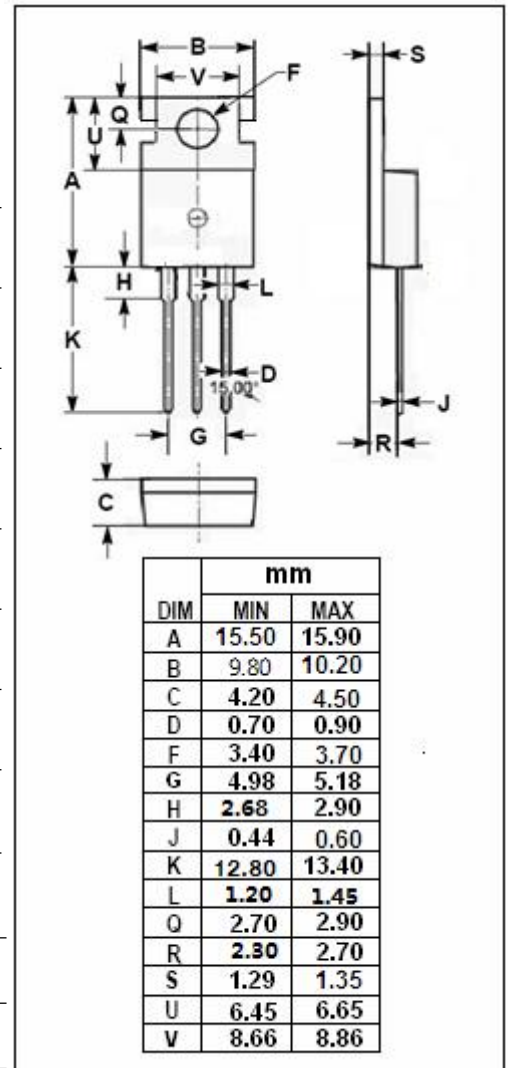
- Drain Current  $-I_D = 8A @ T_C = 25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS} = 600V(\text{Min})$
- Static Drain-Source On-Resistance  
:  $R_{DS(on)} = 1 \Omega (\text{Max})$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation


**APPLICATIONS**

- Switching application

**ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )**

| SYMBOL    | PARAMETER                              | VALUE    | UNIT       |
|-----------|--|----------|------------|
| $V_{DSS}$ | Drain-Source Voltage                   | 600      | V          |
| $V_{GS}$  | Gate-Source Voltage-Continuous         | $\pm 30$ | V          |
| $I_D$     | Drain Current-Continuous               | 8        | A          |
| $I_{DM}$  | Drain Current-Single Pluse             | 32       | A          |
| $P_D$     | Total Dissipation @ $T_C = 25^\circ C$ | 100      | W          |
| $T_J$     | Max. Operating Junction Temperature    | -55~150  | $^\circ C$ |
| $T_{stg}$ | Storage Temperature                    | -55~150  | $^\circ C$ |


**THERMAL CHARACTERISTICS**

| SYMBOL       | PARAMETER                            | MAX  | UNIT         |
|--------------|--------------------------------------|------|--------------|
| $R_{th j-c}$ | Thermal Resistance, Junction to Case | 1.25 | $^\circ C/W$ |

## isc N-Channel MOSFET Transistor

## STP8NM60

## ELECTRICAL CHARACTERISTICS

T<sub>C</sub>=25°C unless otherwise specified

| SYMBOL               | PARAMETER                       | CONDITIONS   | MIN | MAX     | UNIT |
|----------------------|---------------------------------|--|-----|---------|------|
| V <sub>(BR)DSS</sub> | Drain-Source Breakdown Voltage  | V <sub>GS</sub> = 0; I <sub>D</sub> = 1mA  | 600 |         | V    |
| V <sub>GS(th)</sub>  | Gate Threshold Voltage          | V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = 0.25mA  | 3   | 5       | V    |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance      | V <sub>GS</sub> = 10V; I <sub>D</sub> = 2.5A   |     | 1       | Ω    |
| I <sub>GSS</sub>     | Gate-Body Leakage Current       | V <sub>GS</sub> = ±30V; V <sub>DS</sub> = 0  |     | ±100    | nA   |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current | V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0<br>V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0; T <sub>J</sub> = 125°C |     | 1<br>10 | μA   |
| V <sub>SD</sub>      | Forward On-Voltage              | I <sub>S</sub> = 5A; V <sub>GS</sub> =0  |     | 1.5     | V    |

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